

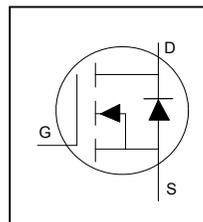
HEXFET® Power MOSFET

Application

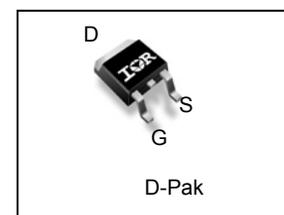
- Optimized for UPS/Inverter Applications
- Low Voltage Power Tools

Benefits

- Fully Characterized Avalanche Voltage and Current
- Lead-Free, RoHS Compliant



V_{DS}	30	V
R_{DS(on)} max (@ V _{GS} = 10V)	2.2	mΩ
(@ V _{GS} = 4.5V)	3.1	
Q_g (typical)	40	nC
I_D (Silicon Limited)	179 ①	A
I_D (Package Limited)	90A	



G	D	S
Gate	Drain	Source

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRFR8314PbF	D-Pak	Tape and Reel	2000	IRFR8314TRPbF

Absolute Maximum Rating

Symbol	Parameter	Max.	Units
V _{DS}	Drain-to-Source Voltage	30	V
V _{GS}	Gate-to-Source Voltage	± 20	
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V (Silicon Limited)	179①	A
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V (Silicon Limited)	127①	
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V (Package Limited)	90	
I _{DM}	Pulsed Drain Current ②	357	
P _D @ T _C = 25°C	Maximum Power Dissipation	125	W
P _D @ T _C = 100°C	Maximum Power Dissipation	63	W
	Linear Derating Factor	0.83	W/°C
T _J	Operating Junction and	-55 to + 175	°C
T _{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds (1.6mm from case)		

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
R _{θJC}	Junction-to-Case ⑤	—	1.2	°C/W
R _{θJA}	Junction-to-Ambient (PCB Mount) ⑦	—	50	
R _{θJA}	Junction-to-Ambient	—	110	

Notes ① through ⑦ are on page 9

Static @ T_J = 25°C (unless otherwise specified)

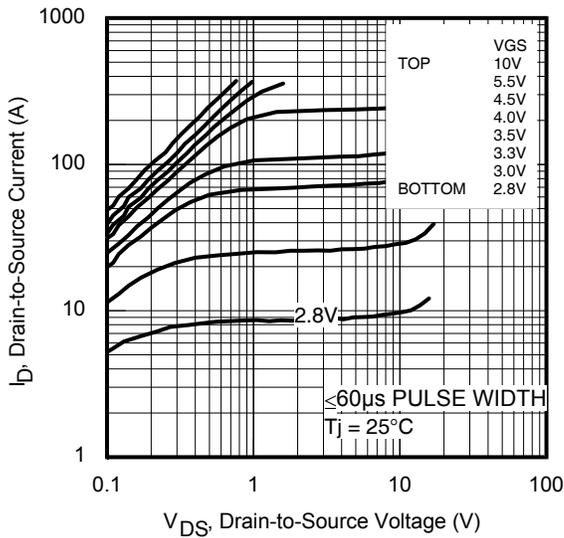
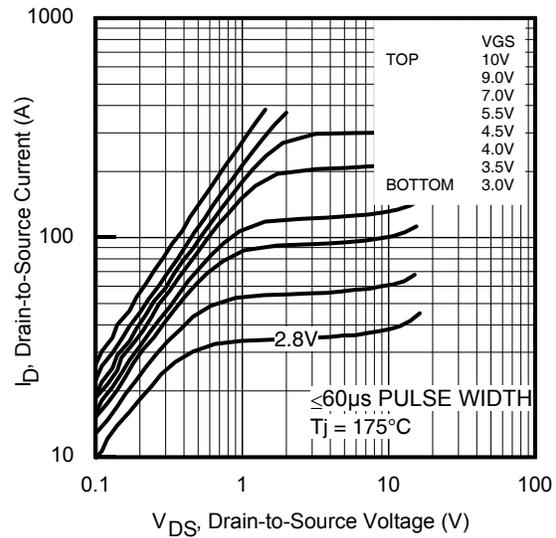
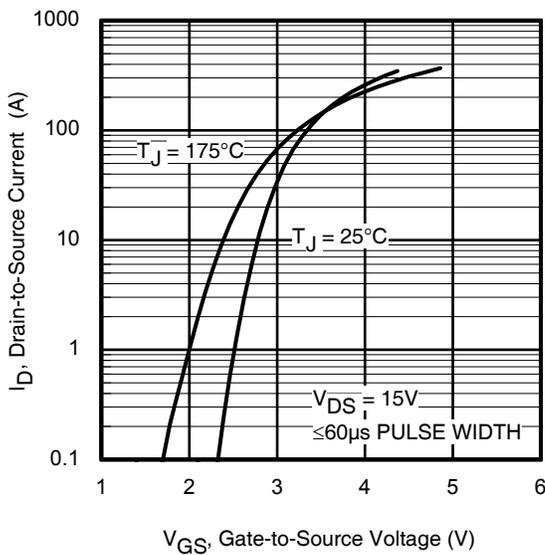
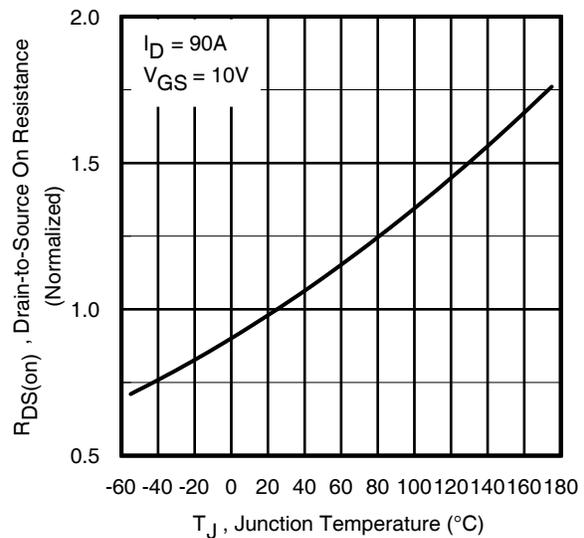
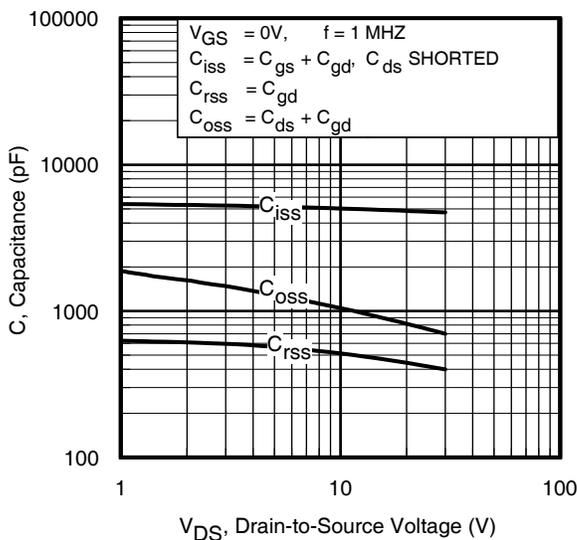
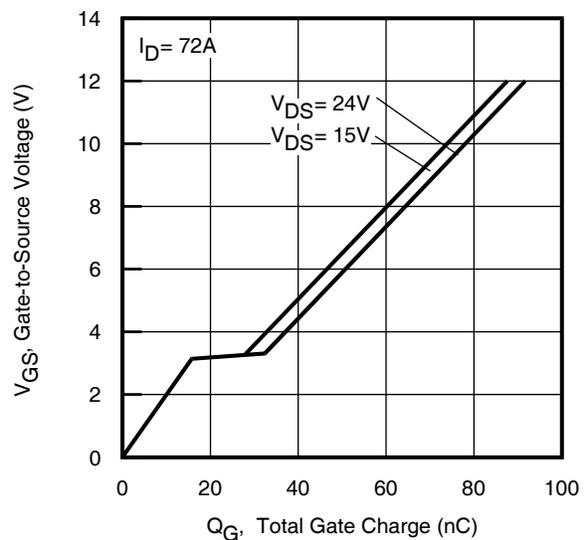
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
BV _{DSS}	Drain-to-Source Breakdown Voltage	30	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔBV _{DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	18	—	mV/°C	Reference to 25°C, I _D = 1mA ②
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	1.6	2.2	mΩ	V _{GS} = 10V, I _D = 90A ④
		—	2.6	3.1		V _{GS} = 4.5V, I _D = 72A ④
V _{GS(th)}	Gate Threshold Voltage	1.2	1.7	2.2	V	V _{DS} = V _{GS} , I _D = 100μA
ΔV _{GS(th)} /ΔT _J	Gate Threshold Voltage Coefficient	—	-7.0	—	mV/°C	
I _{DSS}	Drain-to-Source Leakage Current	—	—	1.0	μA	V _{DS} = 24 V, V _{GS} = 0V
		—	—	150		V _{DS} = 24V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -20V
g _{fs}	Forward Transconductance	189	—	—	S	V _{DS} = 15V, I _D = 72A
Q _g	Total Gate Charge	—	36	54	nC	V _{DS} = 15V V _{GS} = 4.5V I _D = 72A
Q _{gs1}	Pre-V _{th} Gate-to-Source Charge	—	10	—		
Q _{gs2}	Post-V _{th} Gate-to-Source Charge	—	7.7	—		
Q _{gd}	Gate-to-Drain Charge	—	10	—		
Q _{godr}	Gate Charge Overdrive	—	8.3	—		
Q _{sw}	Switch Charge (Q _{gs2} + Q _{gd})	—	20	—		
R _G	Gate Resistance	—	2.0	—		
t _{d(on)}	Turn-On Delay Time	—	19	—	ns	V _{DD} = 15V I _D = 72A R _G = 1.8Ω V _{GS} = 4.5V ④
t _r	Rise Time	—	98	—		
t _{d(off)}	Turn-Off Delay Time	—	28	—		
t _f	Fall Time	—	30	—		
C _{iss}	Input Capacitance	—	4945	—	pF	V _{GS} = 0V V _{DS} = 15V f = 1.0MHz
C _{oss}	Output Capacitance	—	908	—		
C _{rss}	Reverse Transfer Capacitance	—	493	—		

Avalanche Characteristics

E _{AS} (Thermally limited)	Single Pulse Avalanche Energy ③	180	mJ
E _{AS} (tested)	Single Pulse Avalanche Energy Tested Value ⑥	279	
I _A	Avalanche Current	72	A

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode) ②	—	—	179①	A	MOSFET symbol showing the integral reverse p-n junction diode.
I _{SM}	Pulsed Source Current (Body Diode) ②	—	—	357		
V _{SD}	Diode Forward Voltage	—	—	1.0	V	T _J = 25°C, I _S = 72A, V _{GS} = 0V ④
t _{rr}	Reverse Recovery Time	—	31	47	ns	T _J = 25°C I _F = 72A, V _{DD} = 15V
Q _{rr}	Reverse Recovery Charge	—	87	130	nC	di/dt = 360A/μs ④


Fig 1. Typical Output Characteristics

Fig 2. Typical Output Characteristics

Fig 3. Typical Transfer Characteristics

Fig 4. Normalized On-Resistance vs. Temperature

Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

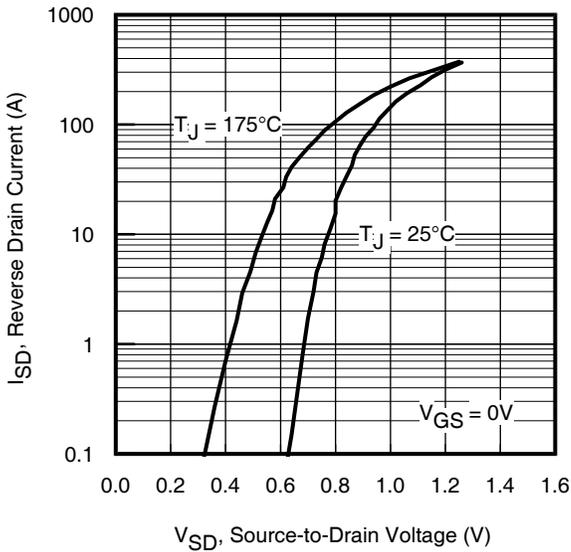


Fig 7. Typical Source-Drain Diode Forward Voltage

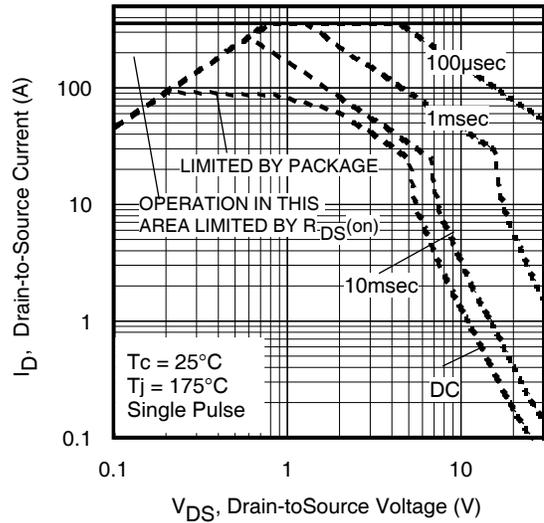


Fig 8. Maximum Safe Operating Area

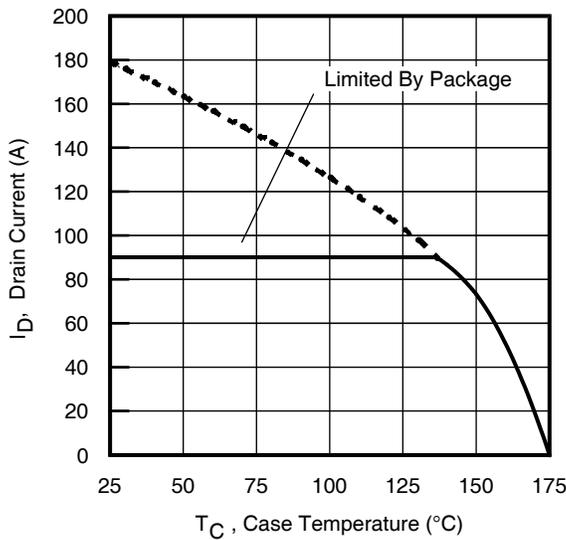


Fig 9. Maximum Drain Current vs. Case Temperature

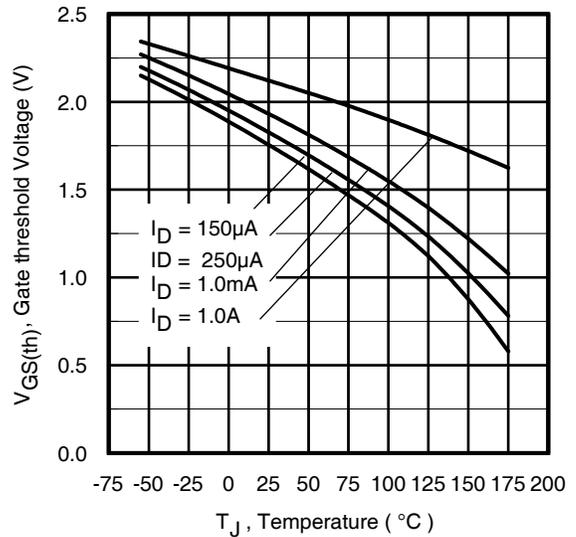


Fig 10. Threshold Voltage vs. Temperature

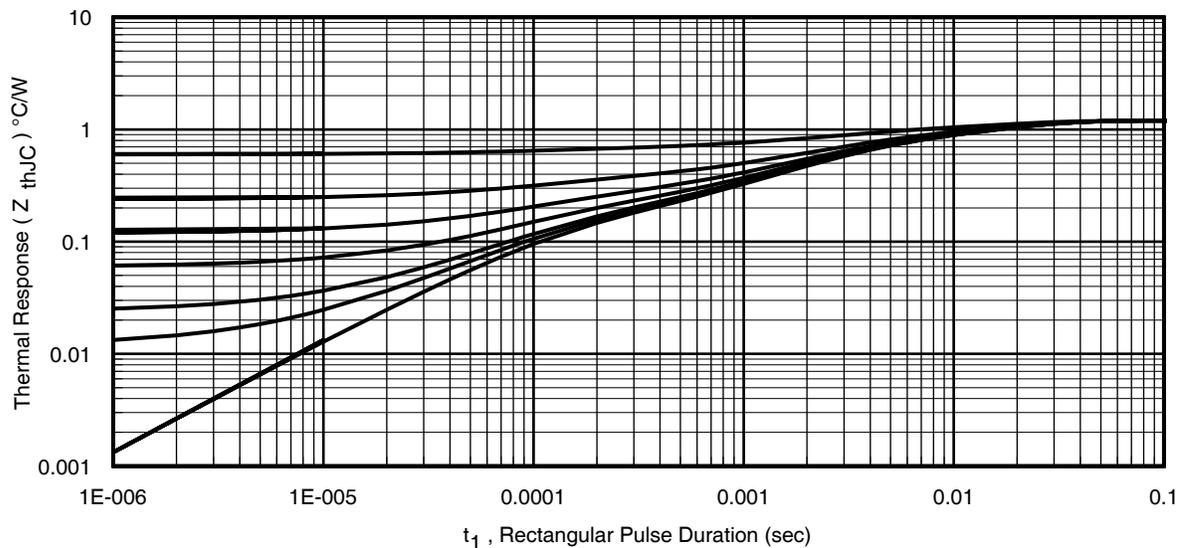


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

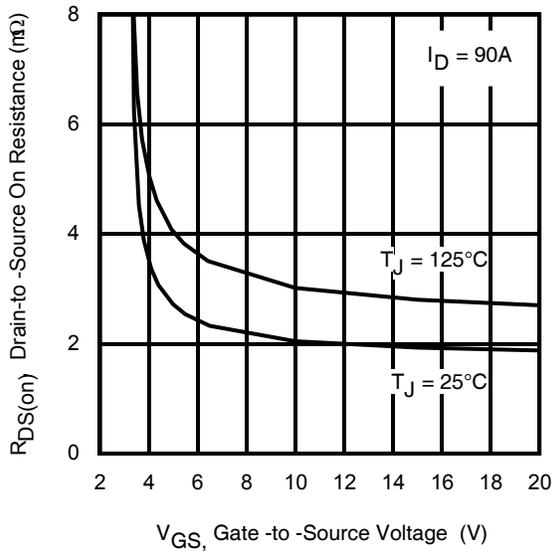


Fig 12. Typical On-Resistance vs. Gate Voltage

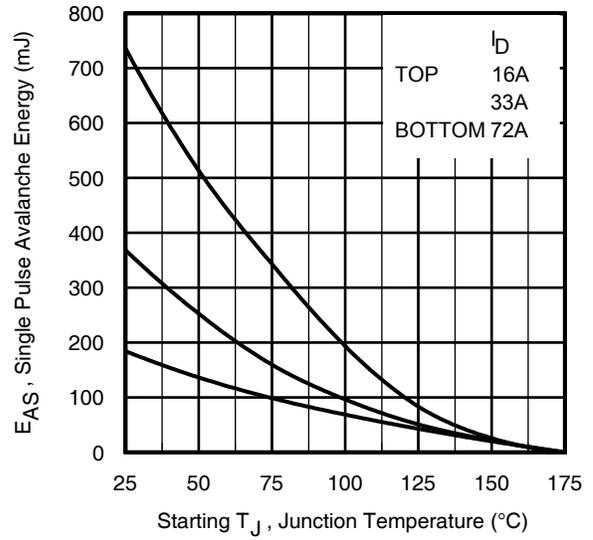
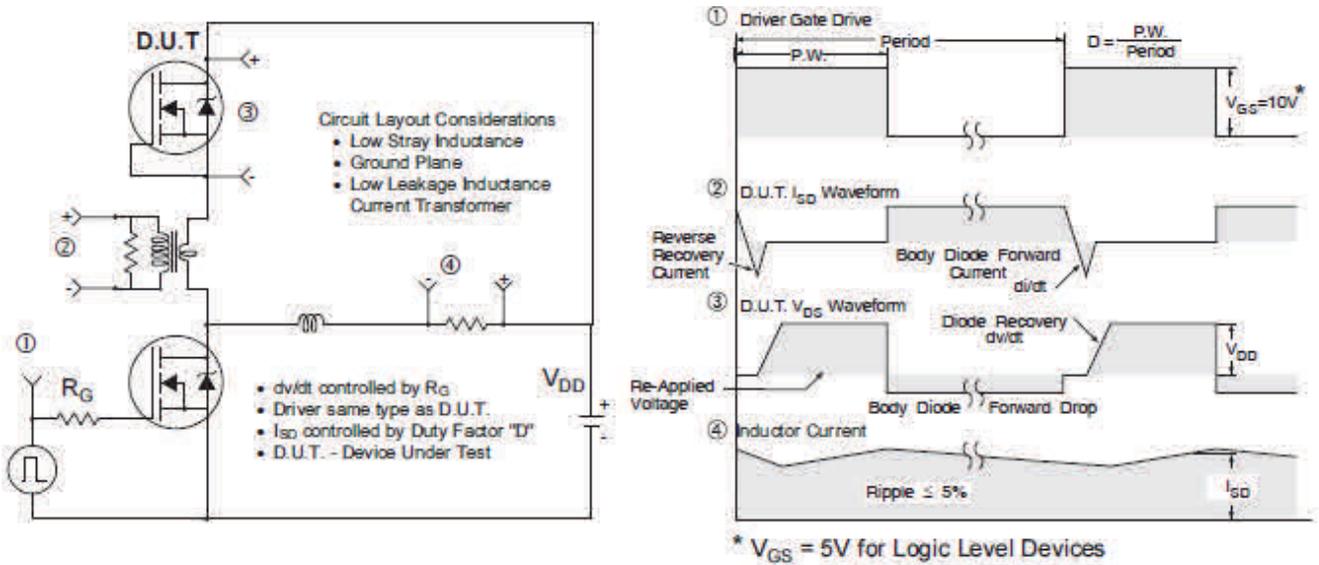
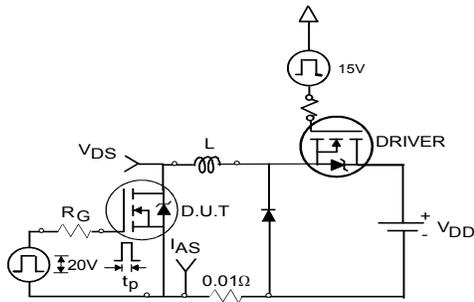
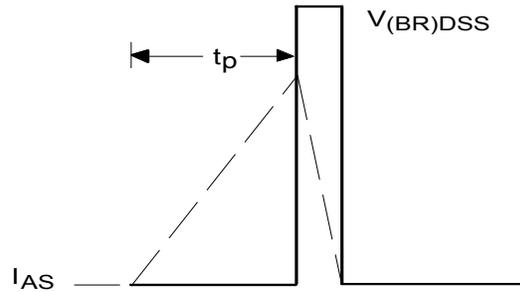
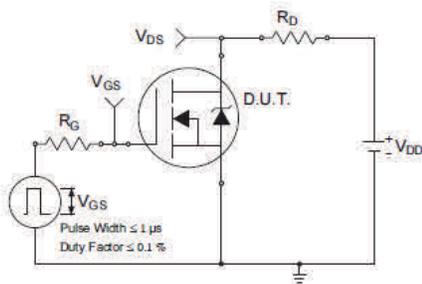
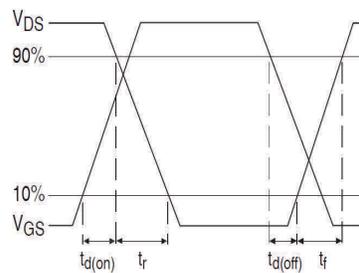
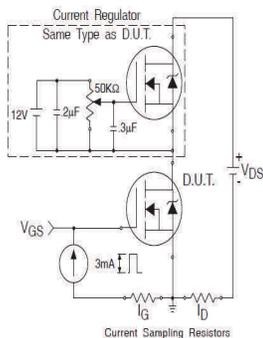
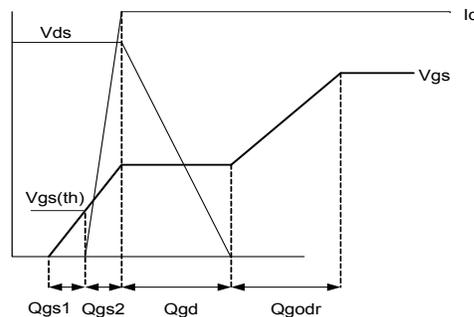
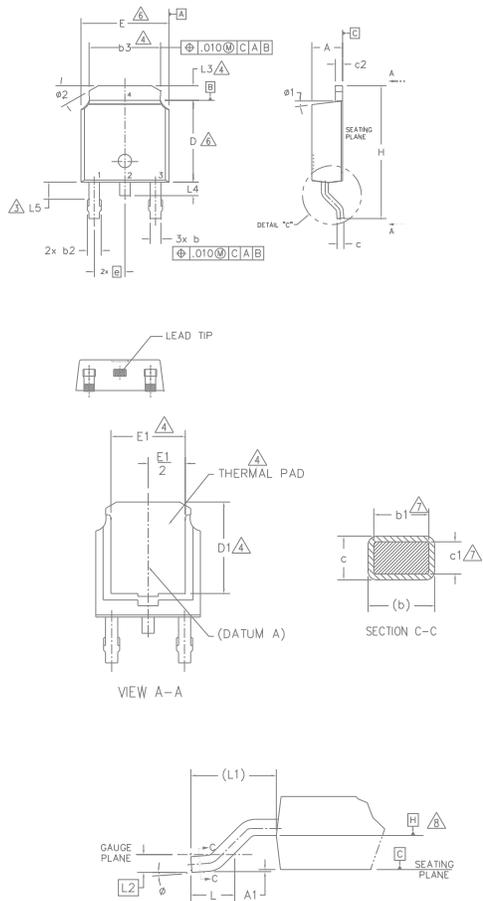


Fig 13. Maximum Avalanche Energy vs. Drain Current


Fig 14. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

Fig 15a. Unclamped Inductive Test Circuit

Fig 15b. Unclamped Inductive Waveforms

Fig 16a. Switching Time Test Circuit

Fig 16b. Switching Time Waveforms

Fig 17a. Gate Charge Test Circuit

Fig 17b. Gate Charge Waveform

D-Pak (TO-252AA) Package Outline Dimensions are shown in millimeters (inches)



- NOTES:
- 1.- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
 - 2.- DIMENSION ARE SHOWN IN INCHES [MILLIMETERS]
 - 3.- LEAD DIMENSION UNCONTROLLED IN L5.
 - 4.- DIMENSION D1, E1, L3 & b3 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
 - 5.- SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 AND 0.10 [0.13 AND 0.25] FROM THE LEAD TIP.
 - 6.- DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .006 [0.15] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
 - 7.- DIMENSION b1 & c1 APPLIED TO BASE METAL ONLY.
 - 8.- DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
 - 9.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1	-	0.13	-	.005	
b	0.64	0.89	.025	.035	
b1	0.64	0.79	.025	.031	7
b2	0.76	1.14	.030	.045	
b3	4.95	5.46	.195	.215	4
c	0.46	0.61	.018	.024	
c1	0.41	0.56	.016	.022	7
c2	0.46	0.89	.018	.035	
D	5.97	6.22	.235	.245	6
D1	5.21	-	.205	-	4
E	6.35	6.73	.250	.265	6
E1	4.32	-	.170	-	4
e	2.29 BSC		.090 BSC		
H	9.40	10.41	.370	.410	
L	1.40	1.78	.055	.070	
L1	2.74 BSC		.108 REF.		
L2	0.51 BSC		.020 BSC		
L3	0.89	1.27	.035	.050	4
L4	-	1.02	-	.040	
L5	1.14	1.52	.045	.060	3
ø	0"	10"	0"	10"	
ø1	0"	15"	0"	15"	
ø2	25"	35"	25"	35"	

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

IGBT & CoPAK

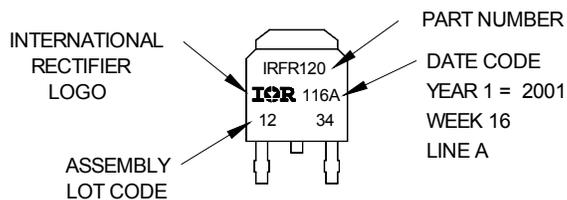
- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

D-Pak (TO-252AA) Part Marking Information

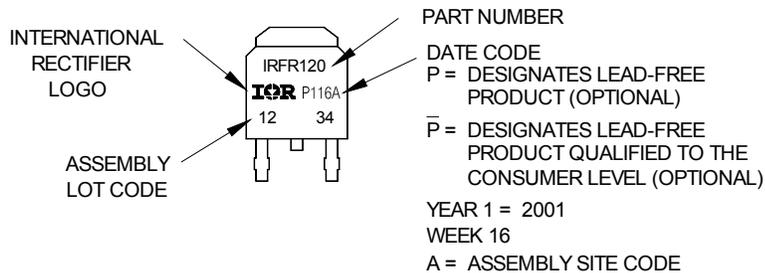
EXAMPLE: THIS IS AN IRFR120
WITH ASSEMBLY
LOT CODE 1234
ASSEMBLED ON WW 16, 2001
IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line position
indicates "Lead-Free"

"P̄" in assembly line position indicates
"Lead-Free" qualification to the consumer-level

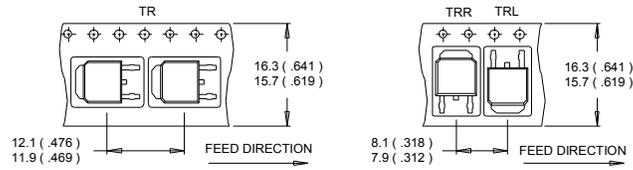


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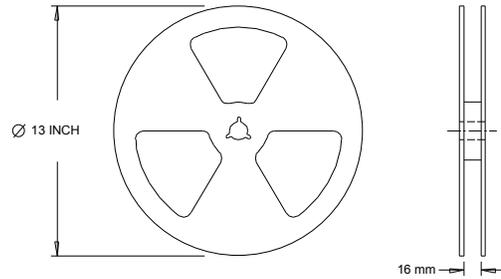


Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

D-Pak (TO-252AA) Tape & Reel Information Dimensions are shown in millimeters (inches)



- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. OUTLINE CONFORMS TO EIA-481.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Qualification Information[†]

Qualification Level	Industrial (per JEDEC JESD47F) ^{††}	
Moisture Sensitivity Level	D-Pak	MSL1
RoHS Compliant	Yes	

† Qualification standards can be found at International Rectifier’s web site: <http://www.irf.com/product-info/reliability/>

†† Applicable version of JEDEC standard at the time of product release.

Notes:

- ① Calculated continuous current based on maximum allowable junction temperature. Bond wire current limit is 90A by source bonding technology. Note that current limitations arising from heating of the device leads may occur with some lead mounting arrangements. (Refer to AN-1140)
- ② Repetitive rating; pulse width limited by max. junction temperature.
- ③ Limited by T_{Jmax} , starting $T_J = 25^{\circ}C$, $L = 0.07mH$, $R_G = 50\Omega$, $I_{AS} = 72A$, $V_{GS} = 10V$.
- ④ Pulse width $\leq 400\mu s$; duty cycle $\leq 2\%$.
- ⑤ R_{θ} is measured at T_J approximately $90^{\circ}C$.
- ⑥ This value determined from sample failure population, starting $T_J = 25^{\circ}C$, $L=0.07mH$, $R_G = 50\Omega$, $I_{AS} = 72A$, $V_{GS} = 10V$.
- ⑦ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994. please refer to application note to AN-994: <http://www.irf.com/technical-info/appnotes/an-994.pdf>

Revision History

Date	Comments
07/01/2014	The Device is active without bulk part which is removed from Table on page 1



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

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- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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